

ABSTRACT OF THE DISCLOSURE

Wet etching is performed on a storage electrode (7) made of ruthenium from above using periodic acid or a cerium ammonium nitrate solution. By using that kind of etching liquid, ruthenium as well as oxide films formed on the surface of the storage
5 electrode (7) can be etched, causing the surface of the storage electrode (7) to be entirely etched. As a result, needle projections having been formed on the top surface of the storage electrode (7) are removed, rounding the top ends of the storage electrode (7). Consequently, the thickness of a dielectric film of a DRAM capacitor to be formed on the storage electrode (7) can be easily made uniform, allowing a reduction in leakage current
10 of the capacitor.